Form 1449 (Modified)	Attorney Docket No: LAM2P279D (Div. of 09/540,418, filed 3/31/2000)	U.S. 10/680,791 ~~Unassigned~~
Information Disclosure Statement By Applicant	Applicant: BENJAMIN	
(Use Several Sheets if Necessary)	Filing Date: October 6, 2003	Group: 2829 ~~Unassigned~~

U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
VN	A	5,936,413	08/1999	Booth et al.			
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	C	4,006,404	02/1977	Szuszczewicz et al.			
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Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Publication Date	Country or Patent Office	Class	Sub-class	Translation Yes	Translation No
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Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
VN	K	W. Lukaszek et al., "*Quantifying Wafer Charging During Via Etch*", May 1996, 1st International Symposium on Plasma Process-Induced Damage.
	L	R. Patrick et al.m "*Study of Pattern Dependent Charging in a High-Density, Inductively Coupled Metal Etcher*" May 1997, 2nd International Symposium on Plasma Process-Induced Damage.
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Examiner	Date Considered
Nguyen	04/12/04

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Form 1449 (Modified)	Attorney Docket No: LAM2P279D (Div. of 09/540,418, filed 3/31/2000)	U.S. 10/660,791 Unassigned
Inf rmation Disclosure Statement By Applicant	Applicant: BENJAMIN	
(Use Several Sheets if Necessary)	Filing Date: October 6, 2003	Group: 2829 ~~Unassigned~~

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Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class
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Foreign Patent or Published Foreign Patent Application

Examiner Initial	No.	Document No.	Date	Country or Patent Office	Class	Sub-class	Translation Yes	Translation No
	L							
	M							
	N							
	O							
	P							

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
	Q	
	R	

Examiner	Date Considered
Nguyen	04/12/04

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.